

Note: This is a draft of a paper submitted for publication. Contents of this paper should not be quoted or referred to without permission of the author(s).

To be presented at the  
*European Materials Research Society*  
*2005 Spring Meeting*  
Strasbourg, France  
May 31 – June 3, 2005

## **Generalized Ellipsometry in Unusual Geometries**

G. E. Jellison, Jr., J. D. Hunn, D. E. Holcomb, and C. M. Rouleau  
Oak Ridge National Laboratory, Oak Ridge, TN 37831-6030

Submitted January 2005

The submitted manuscript has been authored by a contractor of the U.S. Government under contract No. DE-AC05-00OR22725. Accordingly, the U.S. Government retains a nonexclusive, royalty-free license to publish or reproduce the published form of this contribution, or allow others to do so, for U.S. Government purposes."

Prepared by the  
SOLID STATE DIVISION  
OAK RIDGE NATIONAL LABORATORY  
Managed by  
UT-BATTELLE, LLC, for the  
U.S. DEPARTMENT OF ENERGY  
Under Contract No. DE-AC05-00OR22725

# Generalized Ellipsometry in Unusual Geometries

G. E. Jellison, Jr., J. D. Hunn, D. E. Holcomb, and C. M. Rouleau  
Oak Ridge National Laboratory, Oak Ridge, TN 37831-6030

Most ellipsometry experiments are performed by impinging polarized light onto a sample at a large angle of incidence, and the results are usually interpreted in terms of thin film thicknesses and isotropic optical functions of the film or substrate. Here, however, we describe briefly generalized ellipsometry experiments performed using the two-modulator generalized ellipsometer (2-MGE) in either the transmission or normal-incidence configuration. In both cases, microscope optics and serial measurements can be used to create an image of the sample comprised of diattenuation, retardation, direction of the fast axis, circular diattenuation, and polarization factor. Three examples will be presented. First, transmission mode measurements are used to determine the birefringence of z-cut crystals by tilting the sample slightly off normal incidence. Second, in transmission, the 2-MGE can also be used to measure birefringence introduced by the application of an external voltage; we will focus on semi-insulating GaAs. Finally, normal incidence 2-MGE measurements can be used to characterize optical cross-polarization generated from anisotropic samples; we will show examples from highly oriented pyrolytic graphite (HOPG) and cross sections of nuclear fuel particles.

\* Research was sponsored in part by the Office of Nuclear Energy, Science and Technology, the Office of Basic Energy Sciences, the National Nuclear Security Administration and Oak Ridge National Laboratory, managed by UT-Battelle, LLC, for the U.S. Department of Energy under contract No. DE-ACO5-00OR22725.

Submitted to Symposium P (Current Trends in Optical and X-Ray Metrology of Advanced Materials for Nanoscale Devices)